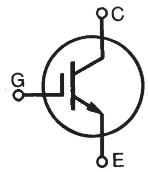
IXYS **Preliminary Technical Information**

XPT™ 650V IGBT GenX3™

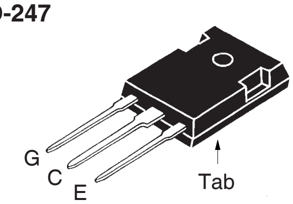
IXYH120N65B3

V_{CES} = 650V
I_{C110} = 120A
$V_{CE(sat)}$ ≤ 1.90V
$t_{fi(typ)}$ = 107ns

Extreme Light Punch Through IGBT for 10-30kHz Switching



TO-247



G = Gate C = Collector
E = Emitter Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 175°C	650	V
V_{CGR}	T_J = 25°C to 175°C, R_{GE} = 1MΩ	650	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C (Chip Capability)	340	A
I_{LRMS}	Terminal Current Limit	160	A
I_{C110}	T_C = 110°C	120	A
I_{CM}	T_C = 25°C, 1ms	770	A
I_A	T_C = 25°C	60	A
E_{AS}	T_C = 25°C	1	J
SSOA **(RBSOA)**	V_{GE} = 15V, T_{VJ} = 150°C, R_G = 2Ω Clamped Inductive Load	I_{CM} = 240 $V_{CE} \le V_{CES}$	A
t_{sc} **(SCSOA)**	V_{GE} = 15V, V_{CE} = 400V, T_J = 150°C R_G = 82Ω, Non Repetitive	8	µs
P_C	T_C = 25°C	1360	W
T_J		-55 ... +175	°C
T_{JM}		175	°C
T_{stg}		-55 ... +175	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
M_d	Mounting Torque	1.13/10	Nm/lb.in
Weight		6	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250µA, V_{GE} = 0V	650			V
$V_{GE(th)}$	I_C = 250µA, V_{CE} = V_{GE}	3.5		6.0	V
I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0V			25	µA
	T_J = 150°C			1	mA
I_{GES}	V_{CE} = 0V, V_{GE} = ±20V			±100	nA
$V_{CE(sat)}$	I_C = 100A, V_{GE} = 15V, Note 1		1.55	1.90	V
	T_J = 150°C		1.77		V

Features

- Optimized for 10-30kHz Switching
- Square RBSOA
- Avalanche Rated
- Short Circuit Capability
- High Current Handling Capability
- International Standard Package

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.
g_{fs}	I_C = 60A, V_{CE} = 10V, Note 1	35	58	S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		6900	pF
C_{oes}			393	pF
C_{res}			146	pF
$Q_{g(on)}$	I_C = 120A, V_{GE} = 15V, V_{CE} = 0.5 • V_{CES}		250	nC
Q_{ge}			52	nC
Q_{gc}			110	nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		30	ns
t_{ri}	I_C = 50A, V_{GE} = 15V		28	ns
E_{on}	V_{CE} = 400V, R_G = 2Ω		1.34	mJ
$t_{d(off)}$	Note 2		168	ns
t_{fi}			107	ns
E_{off}			1.50	mJ
$t_{d(on)}$	**Inductive load, T_J = 150°C**		30	ns
t_{ri}	I_C = 50A, V_{GE} = 15V		30	ns
E_{on}	V_{CE} = 400V, R_G = 2Ω		2.60	mJ
$t_{d(off)}$	Note 2		226	ns
t_{fi}			196	ns
E_{off}			2.20	mJ
R_{thJC}				0.11 °C/W
R_{thCS}			0.21	°C/W

Notes:
1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(clamp), T_J or R_G.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

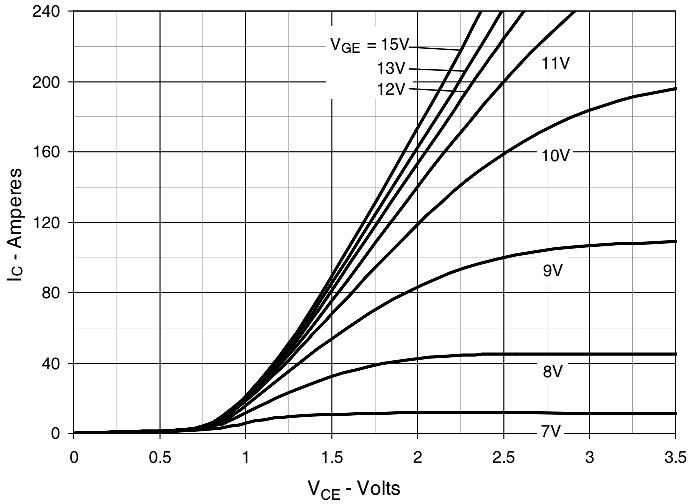


Fig. 1. Output Characteristics @ T_J = 25°C

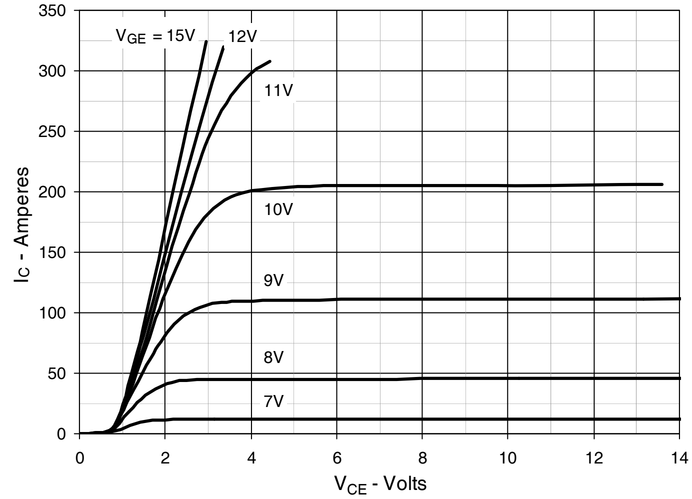


Fig. 2. Extended Output Characteristics @ T_J = 25°C

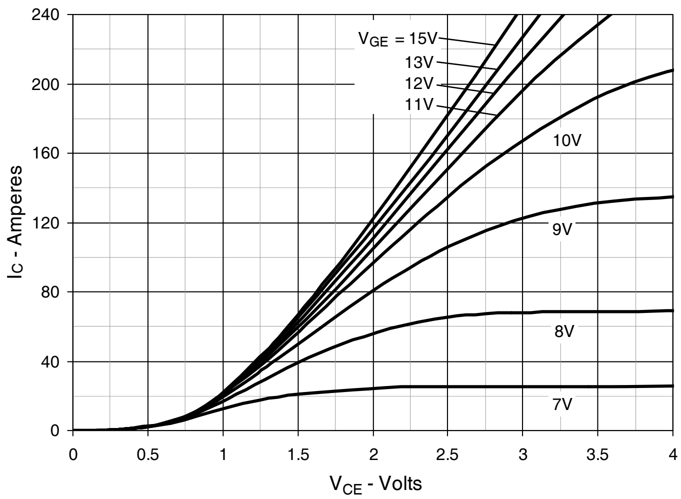


Fig. 3. Output Characteristics @ T_J = 150°C

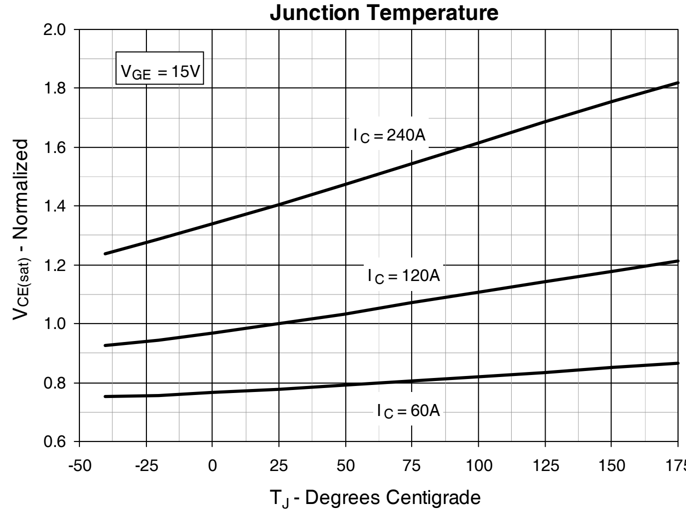


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

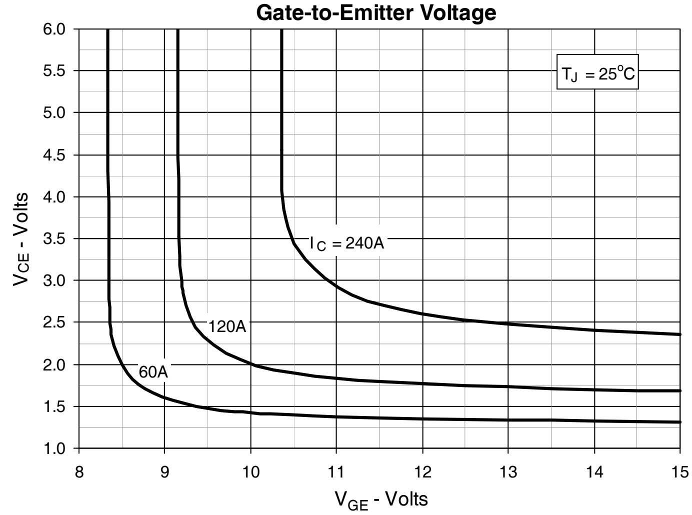


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

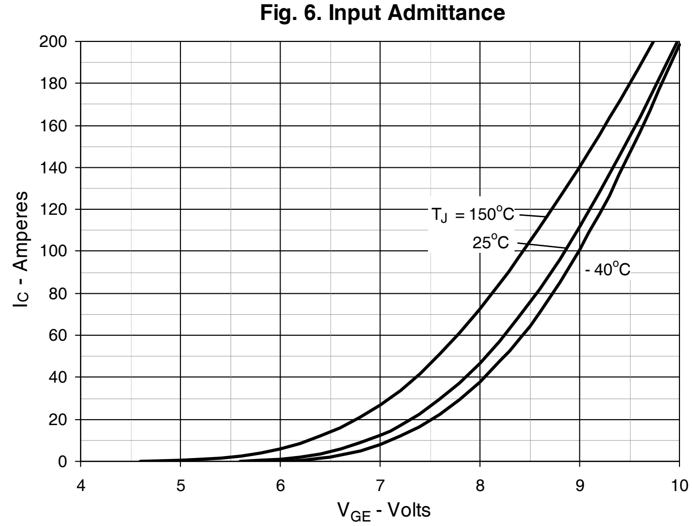


Fig. 6. Input Admittance

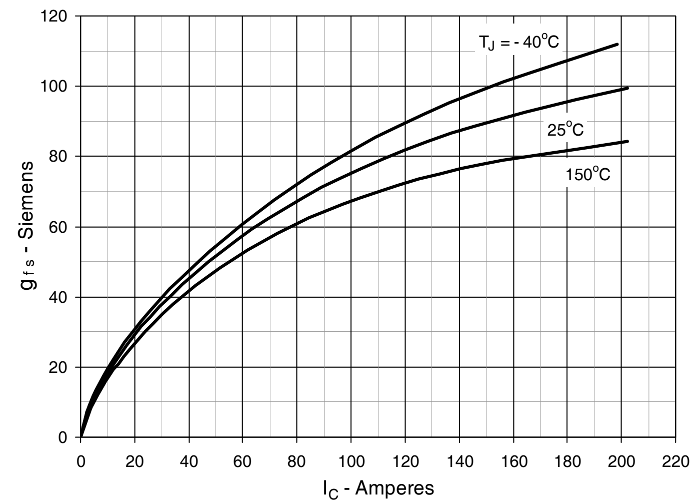


Fig. 7. Transconductance

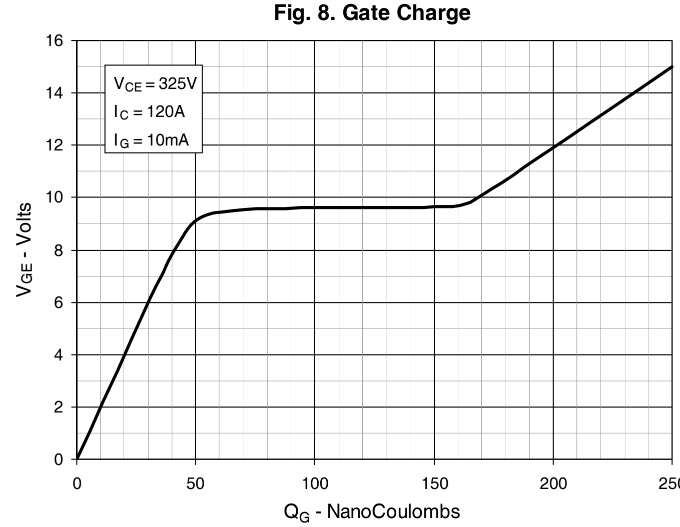


Fig. 8. Gate Charge

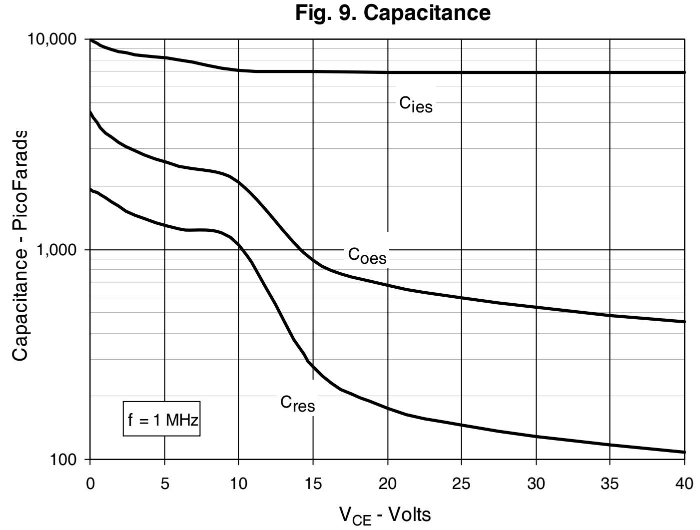


Fig. 9. Capacitance

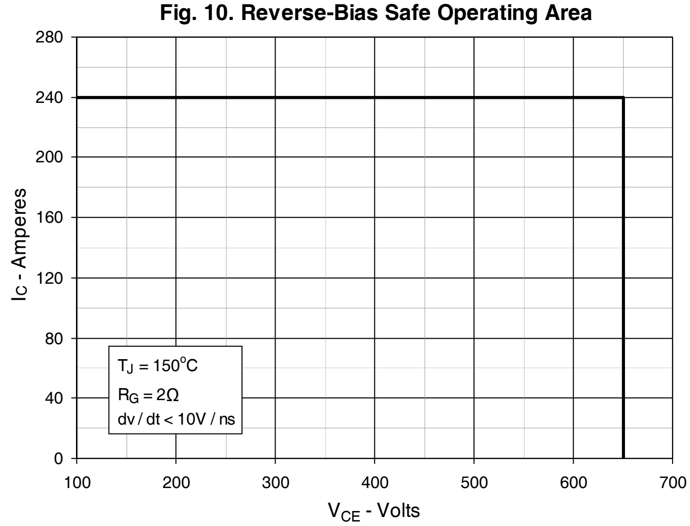


Fig. 10. Reverse-Bias Safe Operating Area

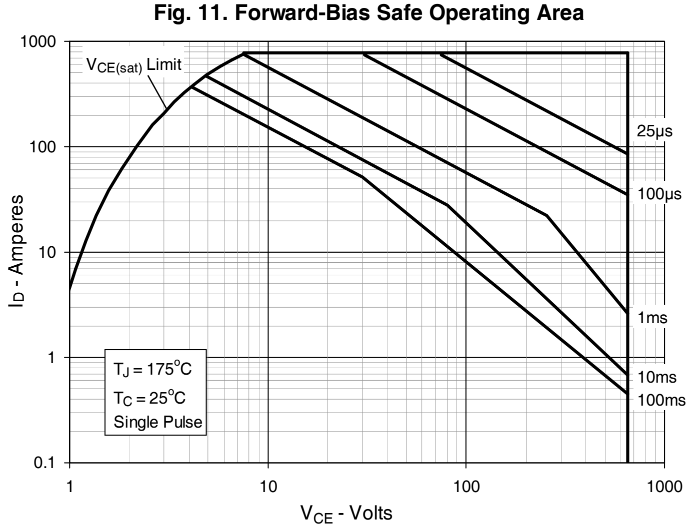


Fig. 11. Forward-Bias Safe Operating Area

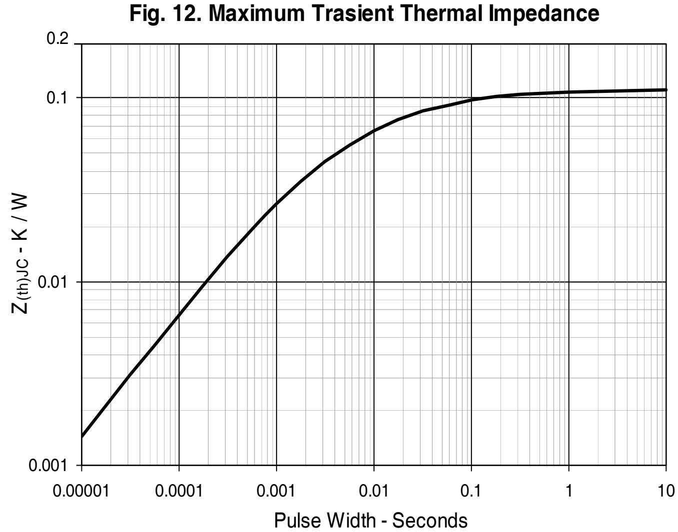


Fig. 12. Maximum Trasient Thermal Impedance

Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance

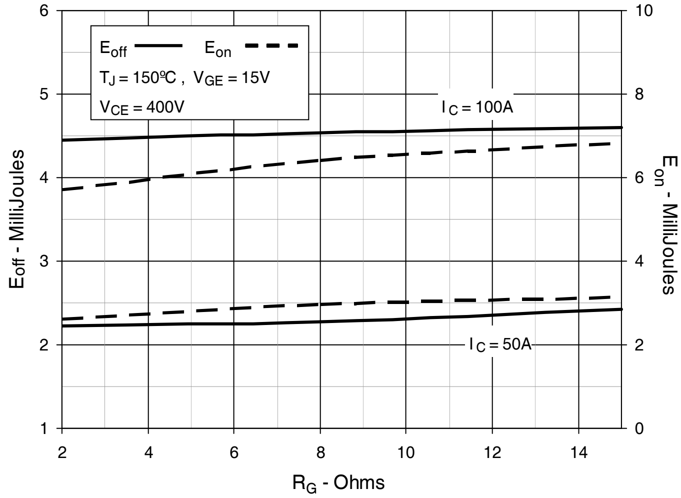


Fig. 14. Inductive Switching Energy Loss vs. Collector Current

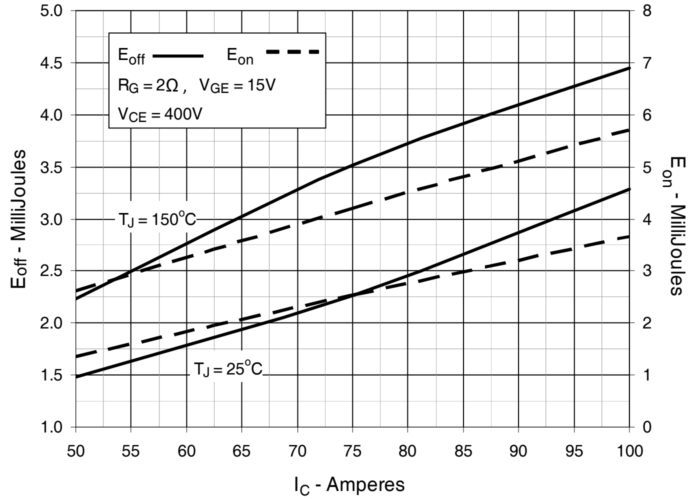


Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature

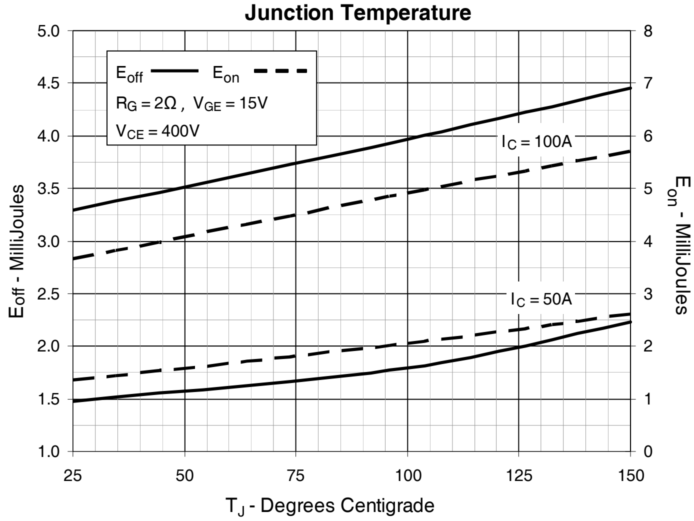


Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance

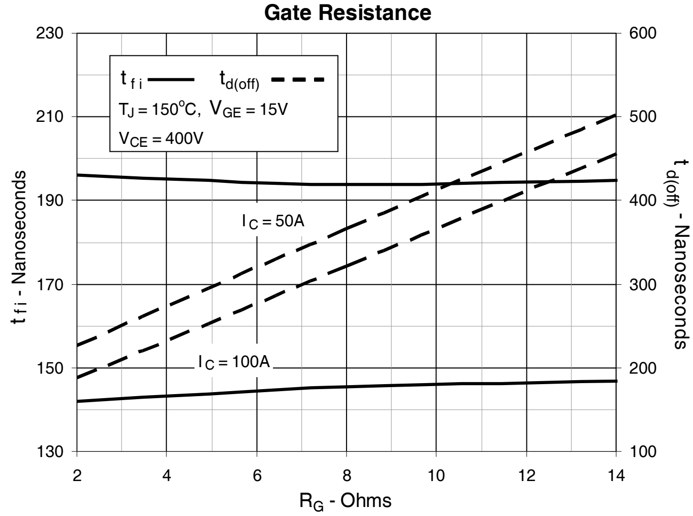


Fig. 17. Inductive Turn-off Switching Times vs. Collector Current

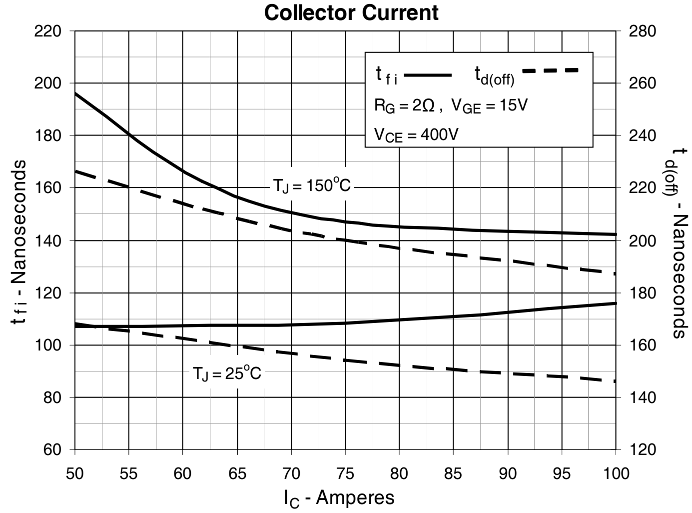


Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature

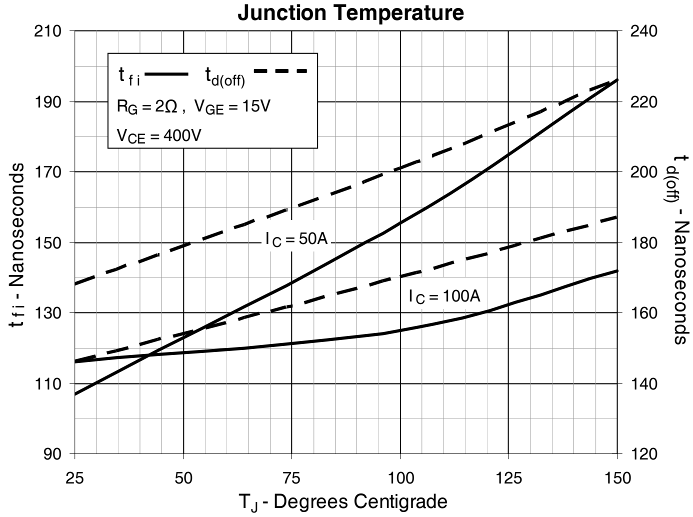


Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance

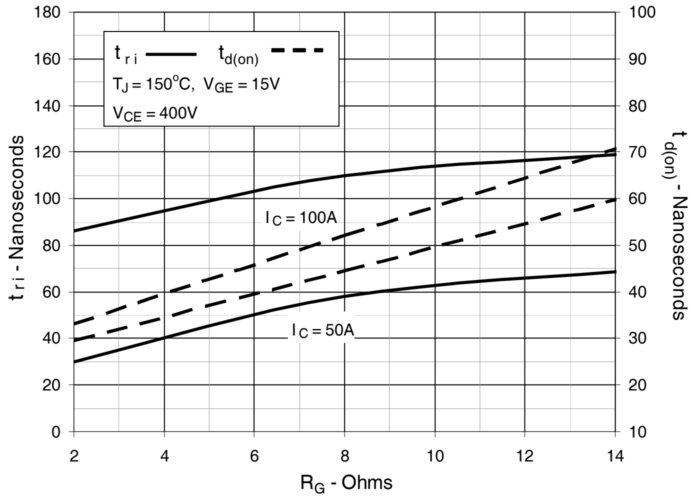


Fig. 20. Inductive Turn-on Switching Times vs. Collector Current

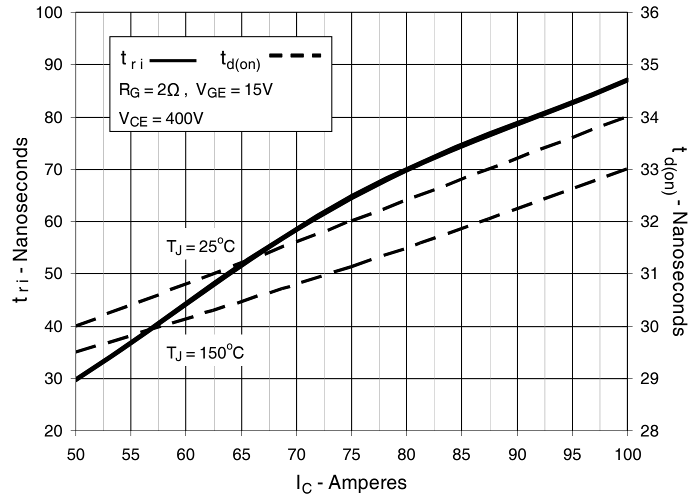
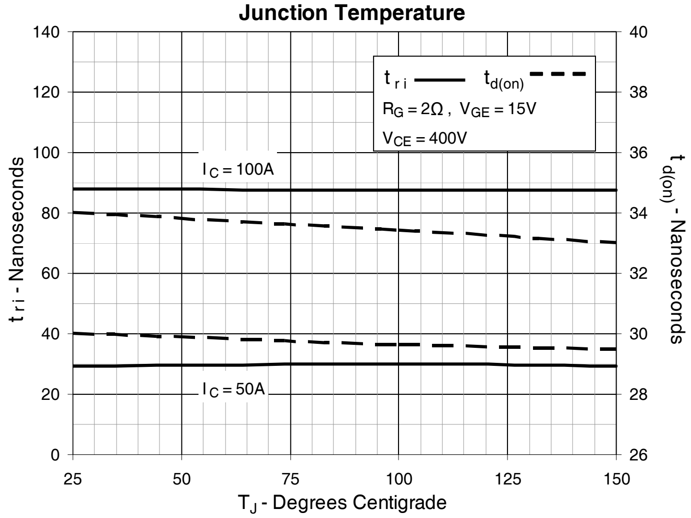
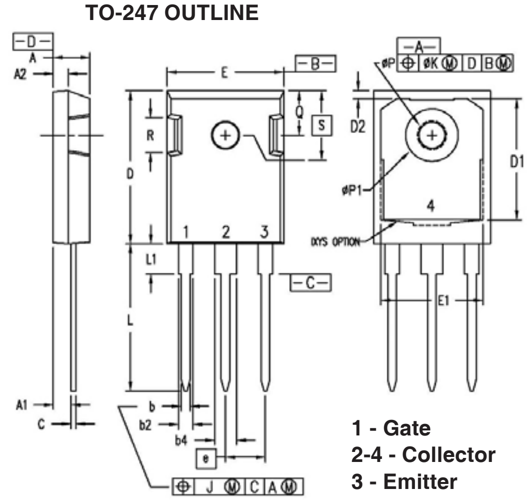


Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature



TO-247 OUTLINE



1 - Gate
2-4 - Collector
3 - Emitter

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.545	.565	13.84	14.35
e	.215 BSC		5.45 BSC	
J	--	.010	--	0.25
K	--	.025	--	0.64
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
øP	.140	.144	3.55	3.65
øP1	.275	.290	6.99	7.37
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.242 BSC		6.15 BSC	

NOTE: This drawing will meet all dimensions requirement of JEDEC outlines TO-247 AD (R-PSIP-F3)